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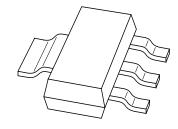
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PZTA92 PNP high-voltage transistor

Product specification Supersedes data of 1997 May 22 1999 Apr 14



PNP high-voltage transistor

PZTA92

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

APPLICATIONS

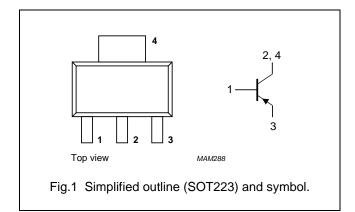
- · Video equipment
- Telephony
- · Professional communication equipment.

DESCRIPTION

PNP high-voltage transistor in a SOT223 plastic package. NPN complement: PZTA42.

PINNING

| PIN | DESCRIPTION |
|------|-------------|
| 1 | base |
| 2, 4 | collector |
| 3 | emitter |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | _ | -300 | V |
| V _{CEO} | collector-emitter voltage | open base | _ | -300 | V |
| V _{EBO} | emitter-base voltage | open collector | _ | -5 | V |
| I _C | collector current (DC) | | _ | -100 | mA |
| I _{CM} | peak collector current | | - | -200 | mA |
| I _{BM} | peak base current | | _ | -100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | _ | 1.2 | W |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| T _j | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

Philips Semiconductors Product specification

PNP high-voltage transistor

PZTA92

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 104 | K/W |
| R _{th j-s} | thermal resistance from junction to soldering point | | 23 | K/W |

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|---|------|------|------|
| I _{CBO} | collector cut-off current | I _E = 0; V _{CB} = -200 V | _ | -20 | nA |
| I _{EBO} | emitter cut-off current | $I_C = 0; V_{BE} = -5 \text{ V}$ | _ | -100 | nA |
| h _{FE} | DC current gain | $I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note 1}$ | 25 | _ | |
| | | $I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note 1}$ | 40 | _ | |
| | | $I_C = -30 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note 1}$ | 25 | _ | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = -20 \text{ mA}; I_B = -2 \text{ mA}$ | _ | -500 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = -20 \text{ mA}; I_B = -2 \text{ mA}$ | _ | -900 | mV |
| C _c | collector capacitance | I _E = 0; V _{CB} = -20 V; f = 1 MHz | _ | 6 | pF |
| f _T | transition frequency | $I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V}; f = 100 \text{ MHz}$ | 50 | _ | MHz |

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

Philips Semiconductors Product specification

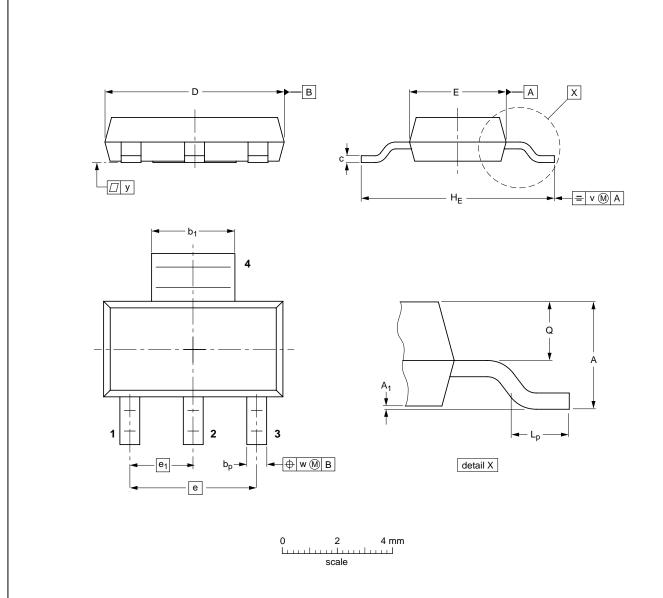
PNP high-voltage transistor

PZTA92

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | bp | b ₁ | С | D | E | е | e ₁ | HE | Lp | Q | v | w | у |
|------|------------|----------------|--------------|----------------|--------------|------------|------------|-----|----------------|------------|------------|--------------|-----|-----|-----|
| mm | 1.8 1.5 | 0.10 0.01 | 0.80 0.60 | 3.1 2.9 | 0.32 0.22 | 6.7 6.3 | 3.7 3.3 | 4.6 | 2.3 | 7.3 6.7 | 1.1 0.7 | 0.95 0.85 | 0.2 | 0.1 | 0.1 |

| OUTLINE | | REFER | ENCES | EUROPEAN ISSUE DATE | | |
|---------|-----|-------|-------|---------------------|-----------------------------|----------------------------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE |
| SOT223 | | | SC-73 | | $ \ \ \bigoplus \big($ | -97-02-28 99-09-13 |

Philips Semiconductors Product specification

PNP high-voltage transistor

PZTA92

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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 Printed in The Netherlands
 115002/00/03/pp6
 Date of release: 1999 Apr 14
 Document order number: 9397 750 05643



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